SN74HCS16507-Q1 Automotive 8-Bit Parallel-Load Shift Registers with Open-Drain Outputs

1 Features

- AEC-Q100 Qualified for automotive applications:
  - Device temperature grade 1: –40°C to +125°C, T_A
  - Device HBM ESD Classification Level 2
  - Device CDM ESD Classifcation Level C6
- Wide operating voltage range: 2 V to 6 V
- Schmitt-trigger inputs allow for slow or noisy input signals
- Low power consumption
  - Typical I_{CC} of 100 nA
  - Typical input leakage current of ±100 nA
- 7.8-mA output drive at 6 V

2 Applications

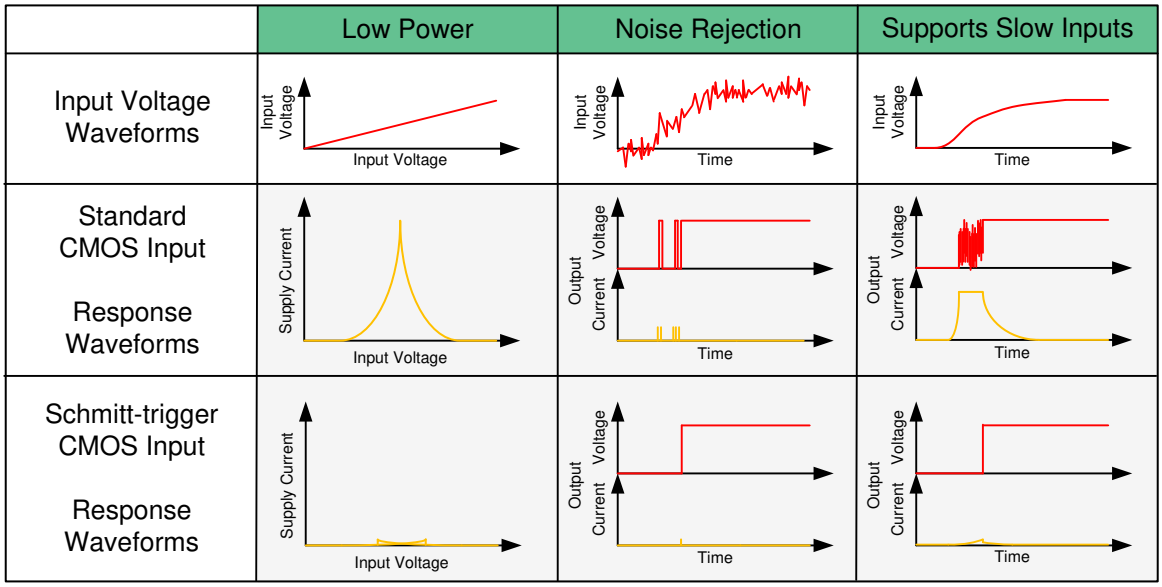
- Increase the Number of Inputs on a Microcontroller

3 Description

The SN74HCS16507-Q1 is a parallel- or serial-in, serial-out 8-bit shift register with open-drain outputs and Schmitt-trigger inputs.

Device Information

PART NUMBER	PACKAGE(1)	BODY SIZE (NOM)
SN74HCS16507PW-Q1	TSSOP (16)	5.00 mm x 4.40 mm
SN74HCS16507D-Q1	SOIC (16)	9.90 mm x 3.90 mm



Benefits of Schmitt-trigger inputs

Table of Contents

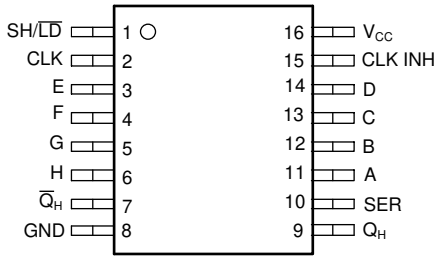
1 Features....1
2 Applications....1
3 Description....1
4 Revision History....2
5 Pin Configuration and Functions....3
6 Specifications....4
6.1 Absolute Maximum Ratings....4
6.2 ESD Ratings....4
6.3 Recommended Operating Conditions....4
6.4 Thermal Information....4
6.5 Electrical Characteristics....5
6.6 Timing Characteristics....5
6.7 Switching Characteristics....6
6.8 Operating Characteristics....7
6.9 Typical Characteristics....8
7 Parameter Measurement Information....9
8 Detailed Description....10
8.1 Overview....10
8.2 Functional Block Diagram....10
8.3 Feature Description....10
8.4 Device Functional Modes....12
9 Application and Implementation....13
9.1 Reference....13
9.2 Typical Application....13
10 Power Supply Recommendations....16
11 Layout....16
11.1 Layout Guidelines....16
11.2 Layout Example....16
12 Device and Documentation Support....17
12.1 Documentation Support....17
12.2 Receiving Notification of Documentation Updates....17
12.3 Support Resources....17
12.4 Trademarks....17
12.5 Electrostatic Discharge Caution....17
12.6 Glossary....17
13 Mechanical, Packaging, and Orderable Information....18

4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES
August 2020	*	Initial Release

5 Pin Configuration and Functions



D or PW Package 14-Pin SOIC or TSSOP Top View

Table 5-1. Pin Functions

PIN		I/O	DESCRIPTION
SOIC or TSSOP NO.	NAME		
1	SH/$\overline{LD}$	I	Enable shifting when input is high, load data when input is low
2	CLK	I	Clock, rising edge triggered
3	E	I	Parallel input E
4	F	I	Parallel input F
5	G	I	Parallel input G
6	H	I	Parallel input H
7	$\overline{Q}_H$	O	Inverted serial output, open drain
8	GND	—	Ground
9	Q_H	O	Serial output, open drain
10	SER	I	Serial input
11	A	I	Parallel input A
12	B	I	Parallel input B
13	C	I	Parallel input C
14	D	I	Parallel input D
15	CLK INH	I	Clock inhibit input
16	V_{CC}	—	Positive supply

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage		–0.5	7	V
I_{IK}	Input clamp current(2)	$V_I < –0.5$ V or $V_I > V_{CC} + 0.5$ V		±20	mA
I_{OK}	Output clamp current(2)	$V_I < –0.5$ V or $V_I > V_{CC} + 0.5$ V		±20	mA
I_O	Continuous output current	V_O = 0 to V_{CC}		35	mA
	Continuous current through V_{CC} or GND			±70	mA
T_J	Junction temperature(3)			150	°C
T_{stg}	Storage temperature		–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
(3) Guaranteed by design.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per AEC Q100-002(1) HBM ESD Classification Level 2	±4000	V
		Charged device model (CDM), per AEC Q100-011 CDM ESD Classification Level C6	±1500	

(1) AEC Q100-002 indicate that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage	2	5	6	V
V_I	Input voltage	0		V_{CC}	V
V_O	Output voltage	0		V_{CC}	V
T_A	Ambient temperature	–40		125	°C

6.4 Thermal Information

THERMAL METRIC(1)		SN74HCS16507-Q1		UNIT
		PW (TSSOP)	D (SOIC)	
		16 PINS	16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	141.2	122.2	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	78.8	80.9	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	85.8	80.6	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	27.7	40.4	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	85.5	80.3	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

6.5 Electrical Characteristics

over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted).

PARAMETER		TEST CONDITIONS		V_{CC}	MIN	TYP	MAX	UNIT
V_{T+}	Positive switching threshold			2 V	0.7		1.5	V
				4.5 V	1.7		3.15	
				6 V	2.1		4.2	
V_{T-}	Negative switching threshold			2 V	0.3		1.0	V
				4.5 V	0.9		2.2	
				6 V	1.2		3.0	
ΔV_T	Hysteresis (V_{T+} - V_{T-})(1)			2 V	0.2		1.0	V
				4.5 V	0.4		1.4	
				6 V	0.6		1.6	
V_{OL}	Low-level output voltage	V_I = V_{IH} or V_{IL}	I_{OL} = 20 µA	2 V to 6 V		0.002	0.1	V
			I_{OL} = 6 mA	4.5 V		0.18	0.30	
			I_{OL} = 7.8 mA	6 V		0.22	0.33	
I_I	Input leakage current	V_I = V_{CC} or 0		6 V		±100	±1000	nA
I_{CC}	Supply current	V_I = V_{CC} or 0, I_O = 0		6 V		0.1	2	µA
C_i	Input capacitance			2 V to 6 V			5	pF

(1) Guaranteed by design.

6.6 Timing Characteristics

C_L = 50 pF; over operating free-air temperature range (unless otherwise noted). See Parameter Measurement Information.

PARAMETER			V_{CC}	Operating free-air temperature (T_A)				UNIT
				25°C		–40°C to 125°C		
				MIN	MAX	MIN	MAX	
f_{clock}	Clock frequency		2 V		49		43	MHz
			4.5 V		130		120	
			6 V		170		150	
t_w	Pulse duration	SH/$\overline{LD}$ low	2 V	6		7		ns
			4.5 V	6		7		
			6 V	6		7		
		CLK high or low	2 V	7		11		
			4.5 V	6		7		
			6 V	6		7		

C_L = 50 pF; over operating free-air temperature range (unless otherwise noted). See Parameter Measurement Information.

PARAMETER			V_{CC}	Operating free-air temperature (T_A)				UNIT
				25°C		–40°C to 125°C		
				MIN	MAX	MIN	MAX	
t_{su}	Setup time	SH/$\overline{LD}$ high before CLK↑	2 V	13		21		ns
			4.5 V	5		7		
			6 V	4		6		
		SER before CLK↑	2 V	8		14		
			4.5 V	4		6		
			6 V	4		6		
		CLK INH low before CLK↑	2 V	6		9		
			4.5 V	4		5		
			6 V	4		5		
		CLK INH high before CLK↑	2 V	6		9		
			4.5 V	4		5		
			6 V	4		5		
		Data before SH/$\overline{LD}$↑	2 V	9		17		
			4.5 V	4		6		
			6 V	4		6		
t_h	Hold time	Ser data after CLK↑	2 V	0		0		ns
			4.5 V	0		0		
			6 V	0		0		
		PAR data after SH/$\overline{LD}$↑	2 V	5		6		
			4.5 V	4		5		
			6 V	3		4		
		SH/$\overline{LD}$ high after CLK↑	2 V	0		0		
			4.5 V	0		0		
			6 V	0		0		

6.7 Switching Characteristics

C_L = 50 pF; over operating free-air temperature range (unless otherwise noted). See Parameter Measurement Information.

PARAMETER		FROM	TO	V_{CC}	Operating free-air temperature (T_A)						UNIT
					25°C			–40°C to 125°C			
					MIN	TYP	MAX	MIN	TYP	MAX	
f_{max}	Max switching frequency			2 V	49			43			MHz
				4.5 V	130			120			
				6 V	170			150			
t_{pd}	Propagation delay	SH/$\overline{LD}$	Q_H or $\overline{Q}_H$	2 V			39			65	ns
				4.5 V			19			24	
				6 V			17			19	
		CLK	Q_H or $\overline{Q}_H$	2 V			32			45	
				4.5 V			16			18	
				6 V			14			16	
		H	Q_H or $\overline{Q}_H$	2 V			30			48	
				4.5 V			15			18	
				6 V			14			16	

C_L = 50 pF; over operating free-air temperature range (unless otherwise noted). See Parameter Measurement Information.

PARAMETER		FROM	TO	V_{CC}	Operating free-air temperature (T_A)						UNIT
					25°C			–40°C to 125°C			
					MIN	TYP	MAX	MIN	TYP	MAX	
t_t	Transition-time		Any output	2 V			9			17	ns
				4.5 V			5			8	
				6 V			4			7	

6.8 Operating Characteristics

over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted).

PARAMETER		TEST CONDITIONS	V_{CC}	MIN	TYP	MAX	UNIT
C_{pd}	Power dissipation capacitance per gate	No load	2 V to 6 V		20		pF

6.9 Typical Characteristics

T_A = 25°C

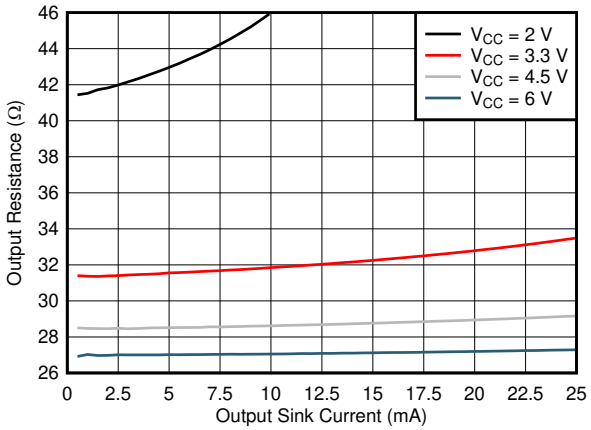


Figure 6-1. Output driver resistance in LOW state.

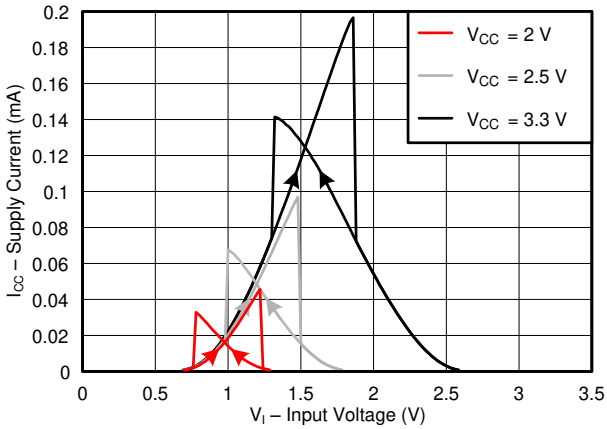


Figure 6-2. Supply current across input voltage, 2-, 2.5-, and 3.3-V supply

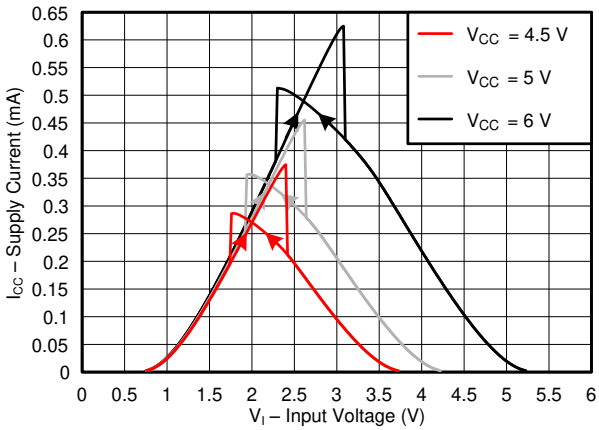


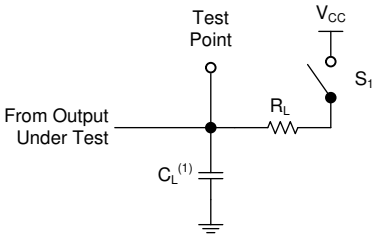
Figure 6-3. Supply current across input voltage, 4.5-, 5-, and 6-V supply

7 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_t < 2.5 ns.

For clock inputs, f_{max} is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.



(1) C_L includes probe and test-fixture capacitance.

Figure 7-1. Load Circuit

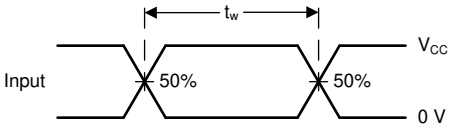


Figure 7-2. Voltage Waveforms, Pulse Duration

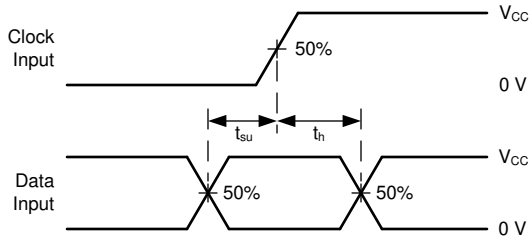
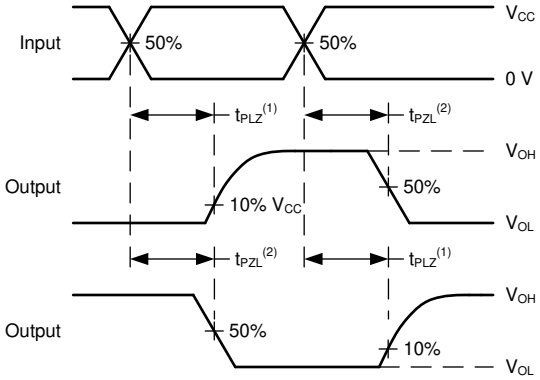


Figure 7-3. Voltage Waveforms, Setup and Hold Times



(1) The greater between t_{PLZ} and t_{PZL} is the same as t_{pd}.

Figure 7-4. Voltage Waveforms Propagation Delays

8 Detailed Description

8.1 Overview

The SN74HCS16507-Q1 is a parallel- or serial-in, serial-out 8-bit shift register with Schmitt-trigger inputs and open-drain outputs.

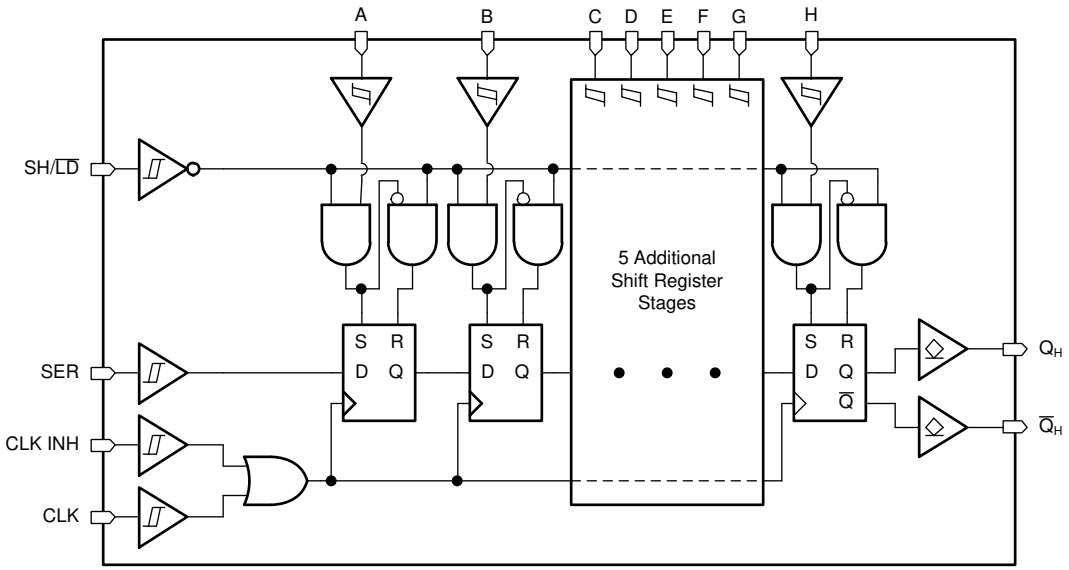
This device has two modes of operation: load data, and shift data.

When the shift or load (SH/$\overline{LD}$) input is held in the low state, the internal registers are loaded with data from the eight lettered inputs (A-H). This operation is asynchronous. In this state, the output (Q) will have the same state as the input H, while the inverted output ($\overline{Q}$) will have the opposite state.

When the shift or load (SH/$\overline{LD}$) input is held in the high state, the internal registers hold their current state until a clock pulse is received. On the rising edge of the clock (CLK) input, data from the serial input will be loaded into the first register, and the data in the internal registers will be shifted by one place. The last register will lose its value. The output (Q) will always be in the same state as the last register, and the inverted output ($\overline{Q}$) will have the opposite state. The clock inhibit (CLK INH) input can be held high to prevent clock pulses from being detected. CLK and CLK INH are interchangable inputs.

8.2 Functional Block Diagram

Figure 8-1. Logic Diagram (Positive Logic) for SN74HCS16507-Q1



8.3 Feature Description

8.3.1 Open-Drain CMOS Outputs

This device includes open-drain CMOS outputs. Open-drain outputs can only drive the output low. When in the high logical state, open-drain outputs will be in a high-impedance state. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

When placed into the high-impedance state, the output will neither source nor sink current, with the exception of minor leakage current as defined in the *Electrical Characteristics* table. In the high-impedance state, the output voltage is not controlled by the device and is dependent on external factors. If no other drivers are connected to the node, then this is known as a floating node and the voltage is unknown. A pull-up resistor can be connected to the output to provide a known voltage at the output while it is in the high-impedance state. The value of the

resistor will depend on multiple factors, including parasitic capacitance and power consumption limitations. Typically, a 10 kΩ resistor can be used to meet these requirements.

Unused open-drain CMOS outputs should be left disconnected.

8.3.2 Balanced CMOS Push-Pull Outputs

This device includes balanced CMOS push-pull outputs. The term "balanced" indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

Unused push-pull CMOS outputs should be left disconnected.

8.3.3 Clamp Diode Structure

The inputs and outputs to this device have both positive and negative clamping diodes as depicted in Electrical Placement of Clamping Diodes for Each Input and Output.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

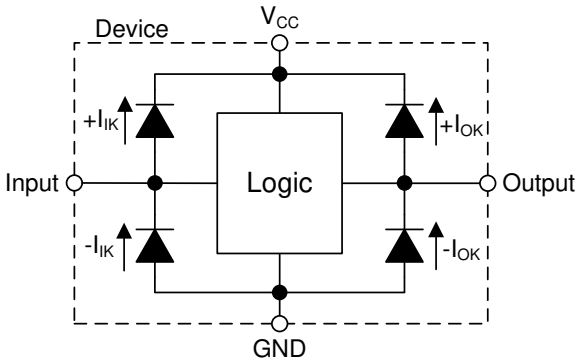


Figure 8-2. Electrical Placement of Clamping Diodes for Each Input and Output

8.3.4 Latching Logic

This device includes latching logic circuitry. Latching circuits commonly include D-type latches and D-type flip-flops, but include all logic circuits that act as volatile memory.

When the device is powered on, the state of each latch is unknown. There is no default state for each latch at start-up.

The output state of each latching logic circuit only remains stable as long as power is applied to the device within the supply voltage range specified in the *Recommended Operating Conditions* table.

8.4 Device Functional Modes

The Operating Mode Table and the Output Function Table list the functional modes of the SN74HCS16507-Q1.

Table 8-1. Operating Mode Table

INPUTS(1)			FUNCTION
SH/$\overline{LD}$	CLK	CLK INH	
L	X	X	Parallel load
H	H	X	No change
H	X	H	No change
H	L	↑	Shift(2)
H	↑	L	Shift(2)

(1) H = High Voltage Level, L = Low Voltage Level, X = Don't Care, ↑ = Low to High transition

(2) Shift : Content of each internal register shifts towards serial output Q_H. Data at SER is shifted into the first register.

Table 8-2. Output Function Table

INTERNAL REGISTERS(1) (2)		OUTPUTS(2)	
A — G	H	Q	$\overline{Q}$
X	L	L	Z
X	H	Z	L

(1) Internal registers refer to the shift registers inside the device. These values are set by either loading data from the parallel inputs, or by clocking data in from the serial input.

(2) H = High Voltage Level, L = Low Voltage Level, X = Don't Care, Z = High Impedance

9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Reference

The SN74HCS16507-Q1 is a parallel-input shift register, which can be used to reduce the number of required inputs on a system controller very significantly in some applications. Parallel data is loaded into the shift register, then the stored data can be loaded into a serial input of the system controller by clocking the shift register.

Multiple shift registers can be cascaded to provide more data inputs while still only using a single serial input to the system controller. This process is primarily limited by the required data input rate and timing characteristics of the selected shift register, as defined in the *Timing Charactestics* and *Switching Charactestics* tables.

An example block diagram is shown for using a single shift register in the *Typical application block diagram* below.

9.2 Typical Application

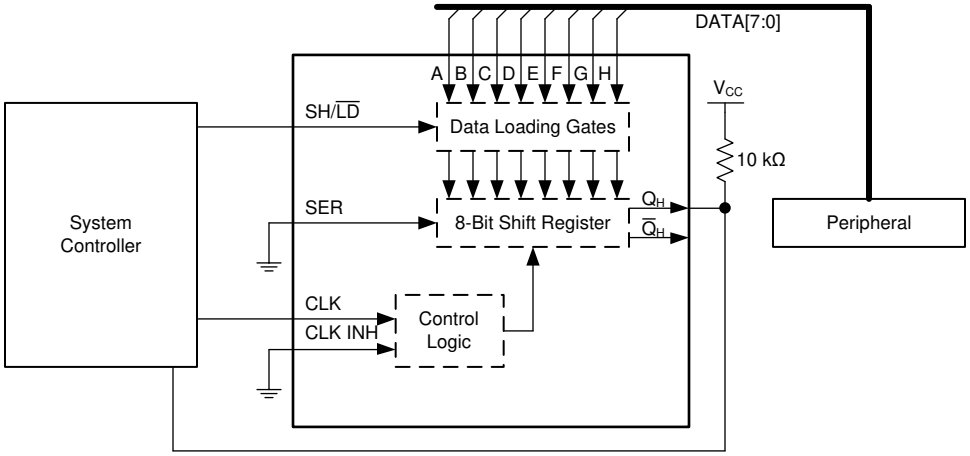


Figure 9-1. Typical application block diagram

9.2.1 Design Requirements

9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics*.

The positive voltage supply must be capable of sourcing current equal to the maximum static supply current, I_{CC}, listed in *Electrical Characteristics* and any transient current required for switching.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74HCS16507-Q1 plus the maximum supply current, I_{CC}, listed in *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current as can be sunk into its ground connection. Be sure not to exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74HCS16507-Q1 can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the datasheet specifications. Larger capacitive loads can be applied, however it is not recommended to exceed 50 pF.

The SN74HCS16507-Q1 can drive a load with total resistance described by $R_L \geq V_O / I_O$, with the output voltage and current defined in the *Electrical Characteristics* table with V_{OL}. When outputting in the high state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V_{CC} pin.

Total power consumption can be calculated using the information provided in CMOS Power Consumption and Cpd Calculation.

Thermal increase can be calculated using the information provided in Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices.

CAUTION

The maximum junction temperature, $T_{J(max)}$ listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

9.2.1.2 Input Considerations

Input signals must cross $V_{t-(min)}$ to be considered a logic LOW, and $V_{t+(max)}$ to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either V_{CC} or ground. These can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input is to be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the SN74HCS16507-Q1, as specified in the *Electrical Characteristics*, and the desired input transition rate. A 10-kΩ resistor value is often used due to these factors.

The SN74HCS16507-Q1 has no input signal transition rate requirements because it has Schmitt-trigger inputs.

Another benefit to having Schmitt-trigger inputs is the ability to reject noise. Noise with a large enough amplitude can still cause issues. To know how much noise is too much, please refer to the $\Delta V_{T(min)}$ in the *Electrical Characteristics*. This hysteresis value will provide the peak-to-peak limit.

Unlike what happens with standard CMOS inputs, Schmitt-trigger inputs can be held at any valid value without causing huge increases in power consumption. The typical additional current caused by holding an input at a value other than V_{CC} or ground is plotted in the *Typical Characteristics*.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.

9.2.1.3 Output Considerations

The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Electrical Characteristics*.

Open-drain outputs can be connected together directly to produce a wired-AND configuration or for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC}.

Refer to *Feature Description* section for additional information regarding the outputs for this device.

9.2.2 Detailed Design Procedure

1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the *Layout* section.
2. Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit, however it will ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74HCS16507-Q1 to the receiving device(s).

3. Ensure the resistive load at the output is larger than (V_{CC} / $I_{O(max)}$) Ω. This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in megaohms; much larger than the minimum calculated above.
4. Thermal issues are rarely a concern for logic gates, however the power consumption and thermal increase can be calculated using the steps provided in the application report, CMOS Power Consumption and Cpd Calculation.

9.2.3 Application Curve

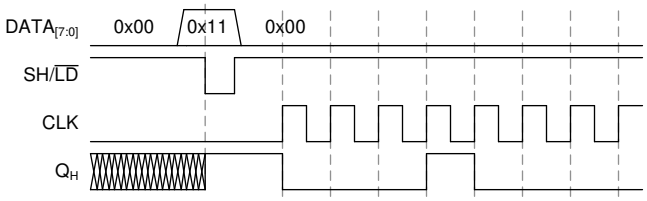


Figure 9-2. Application timing diagram

10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each V_{CC} terminal should have a good bypass capacitor to prevent power disturbance. A 0.1-µF capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1-µF and 1-µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in given example layout image.

11 Layout

11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC}, whichever makes more sense for the logic function or is more convenient.

11.2 Layout Example

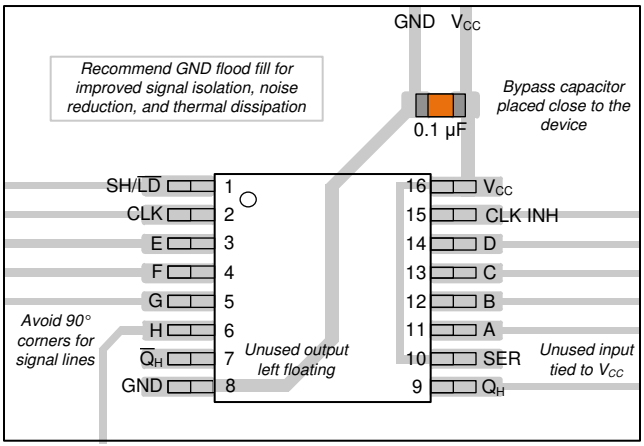


Figure 11-1. Example layout for the SN74HCS16507-Q1 in the PW package.

12 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

- Texas Instruments, *HCMOS Design Considerations* application report (SCLA007)
- Texas Instruments, *CMOS Power Consumption and C_{pd} Calculation* application report (SDYA009)
- Texas Instruments, *Designing With Logic* application report

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

12.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

12.5 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.6 Glossary

TI Glossary	This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN74HCS16507QDRQ1	Active	Production	SOIC (D) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	H16507Q
SN74HCS16507QDRQ1.A	Active	Production	SOIC (D) | 16	2500 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	H16507Q
SN74HCS16507QPWRQ1	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	H16507Q
SN74HCS16507QPWRQ1.A	Active	Production	TSSOP (PW) | 16	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	H16507Q

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

OTHER QUALIFIED VERSIONS OF SN74HCS16507-Q1 :

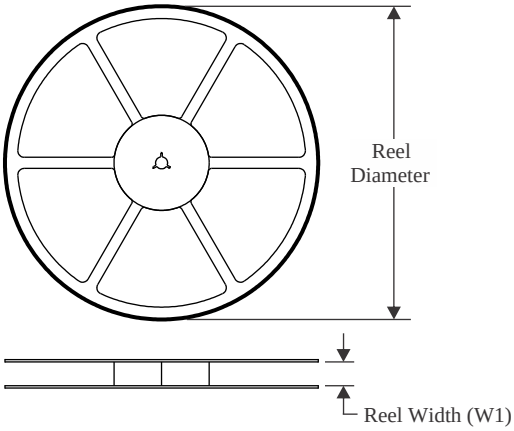
- Catalog : SN74HCS16507

NOTE: Qualified Version Definitions:

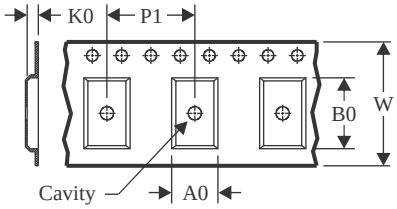
- Catalog - TI's standard catalog product

TAPE AND REEL INFORMATION

REEL DIMENSIONS

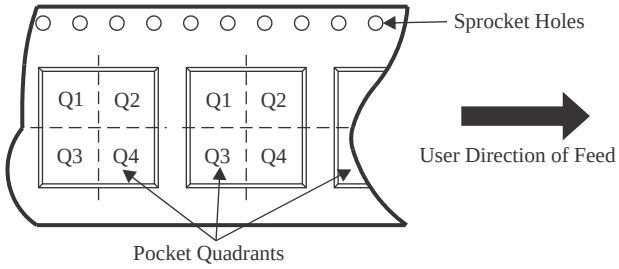


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

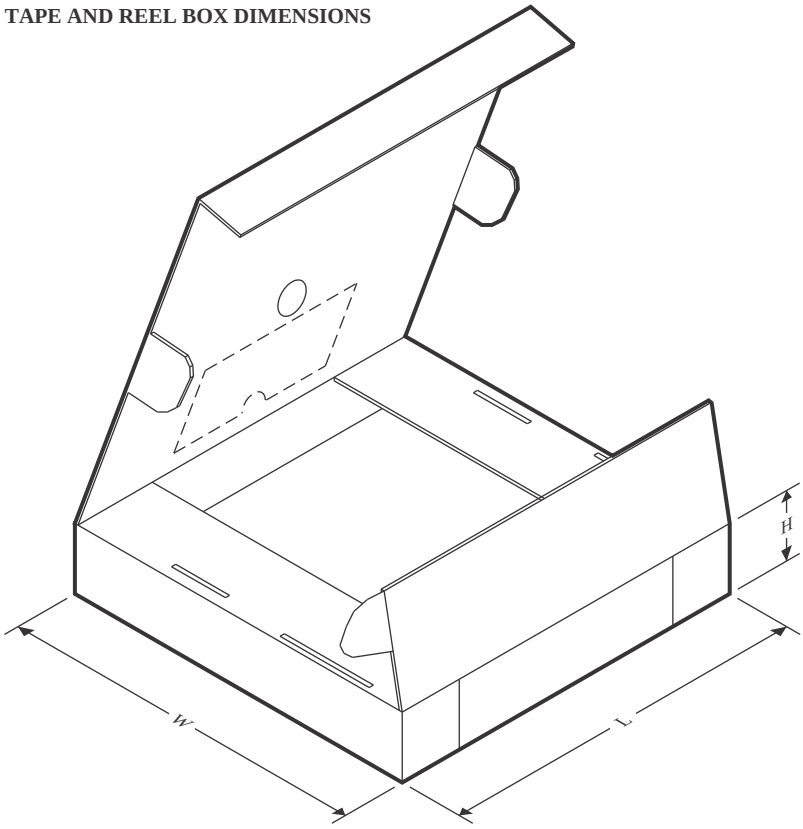
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74HCS16507QDRQ1	SOIC	D	16	2500	330.0	16.4	6.5	10.3	2.1	8.0	16.0	Q1

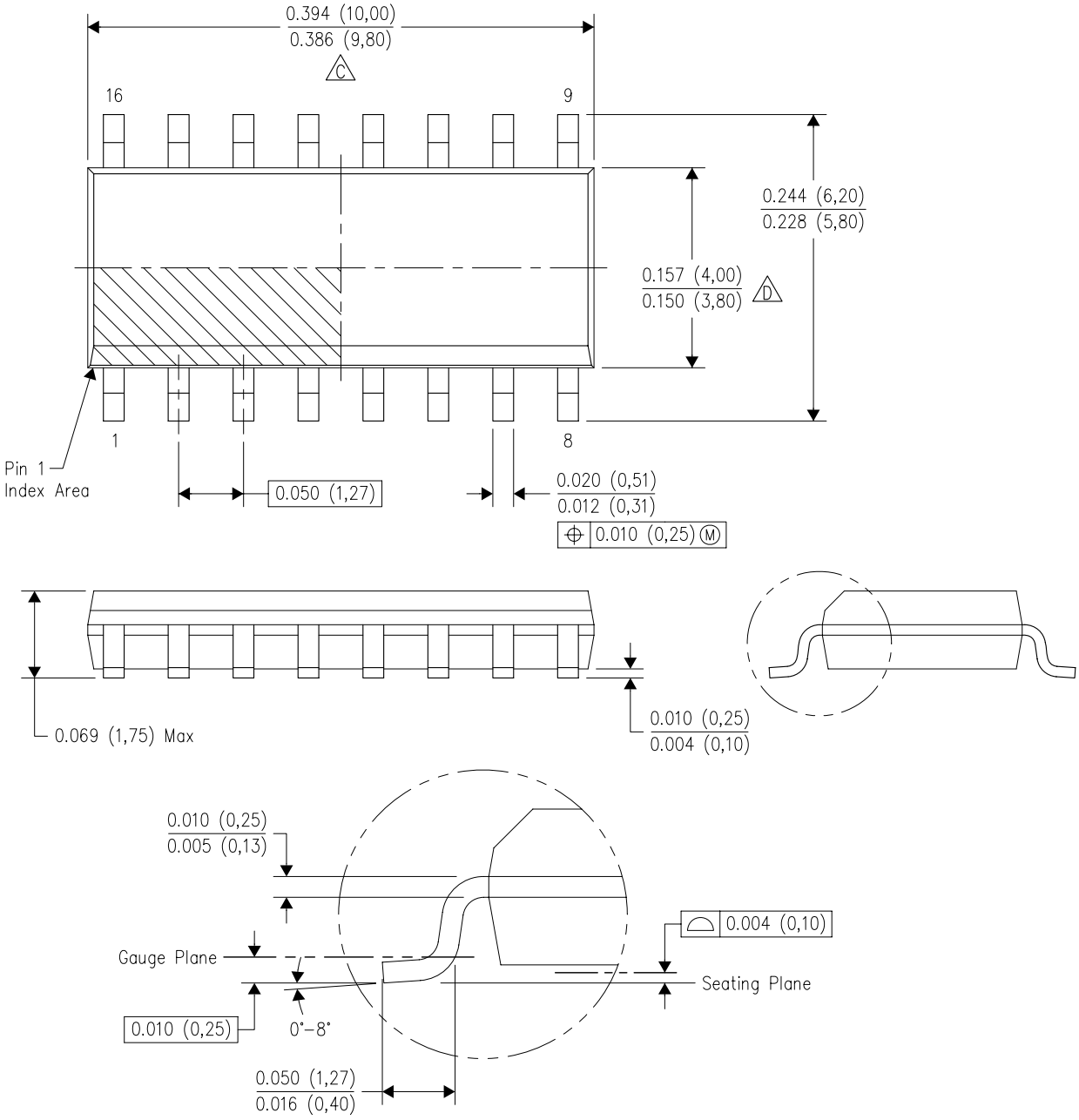
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74HCS16507QDRQ1	SOIC	D	16	2500	353.0	353.0	32.0

D (R–PDSO–G16) PLASTIC SMALL OUTLINE



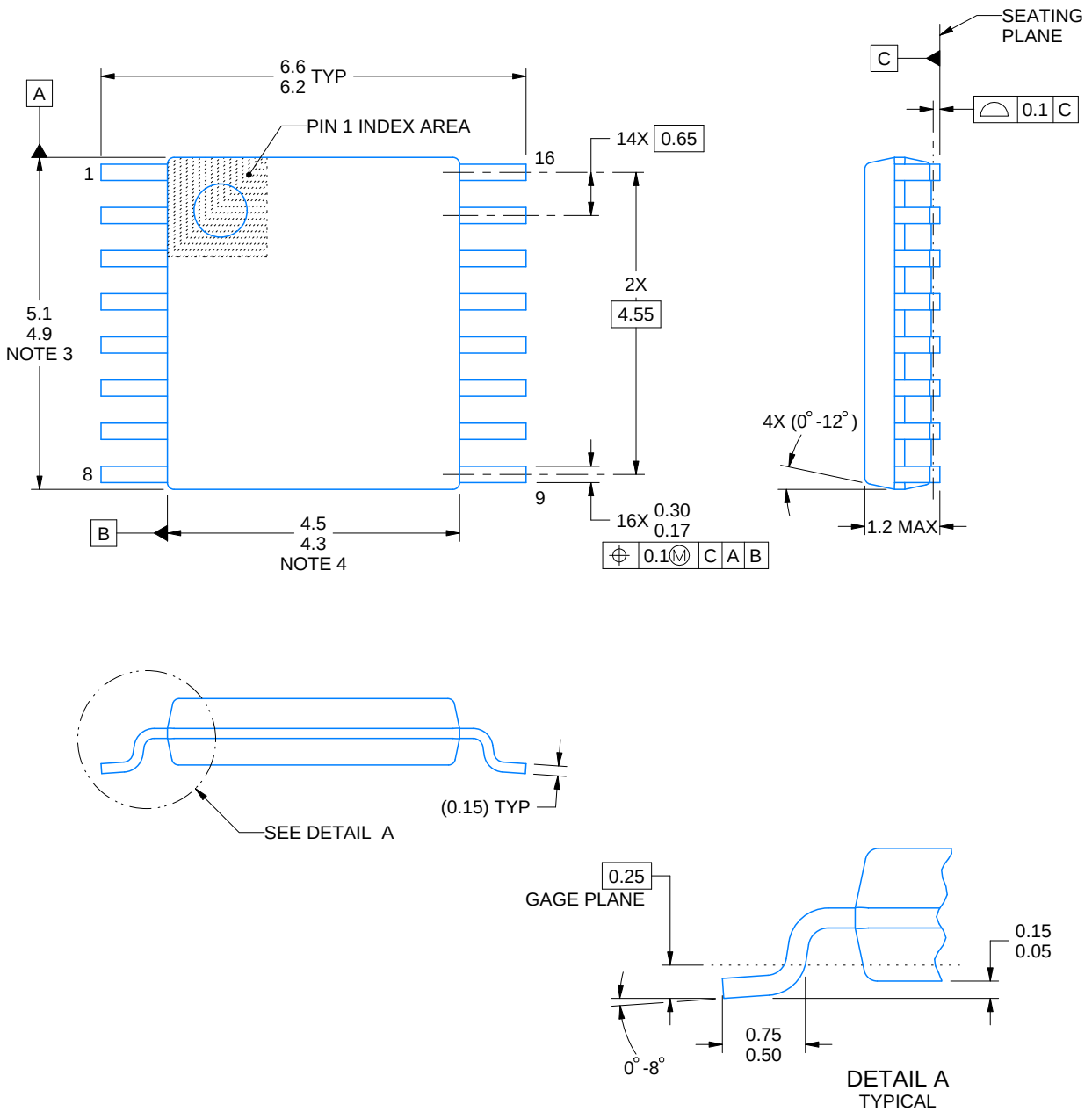
NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS–012 variation AC.

PACKAGE OUTLINE

PW0016A

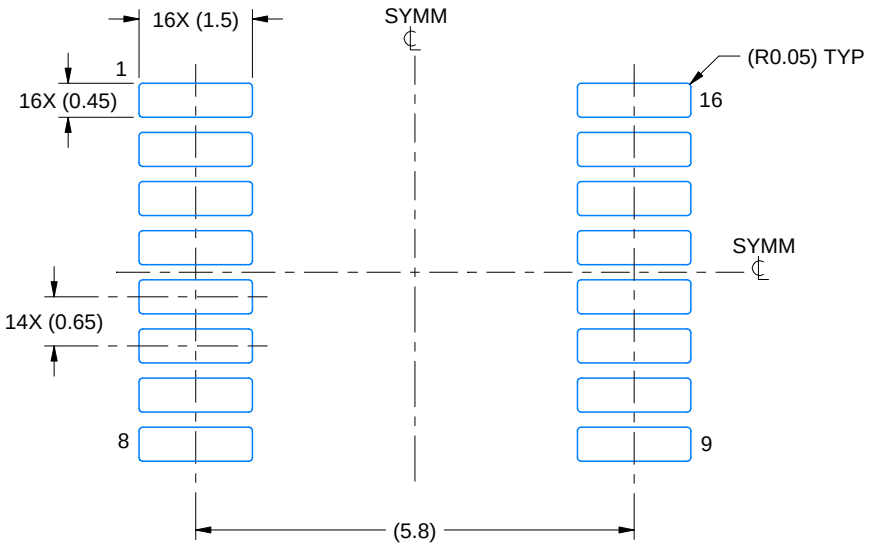
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.



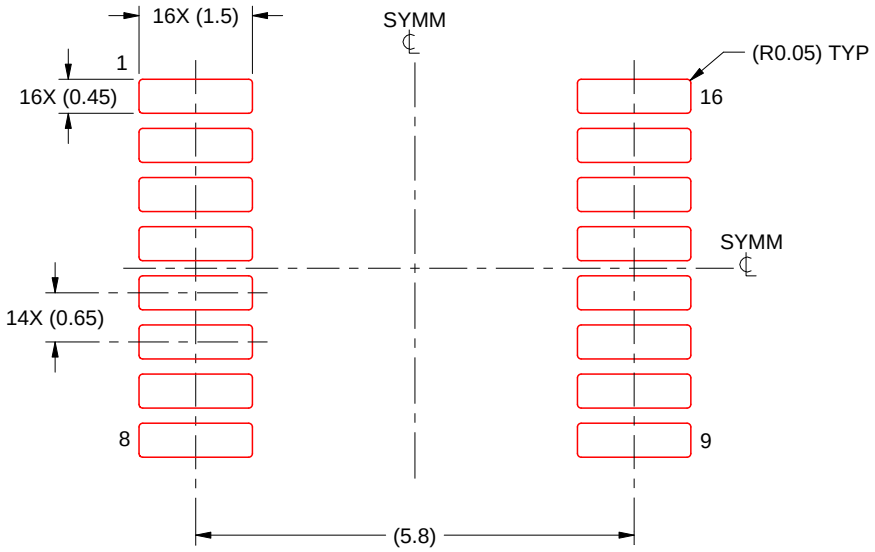
LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

SOLDER MASK DETAILS

4220204/B 12/2023

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220204/B 12/2023

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES “AS IS” AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI’s products are provided subject to TI’s Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI’s provision of these resources does not expand or otherwise alter TI’s applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265